

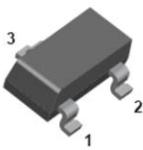
FEATURES

- Low saturation.
- Complementary To FMMT591.
- Excellent H_{FE} Linearity.

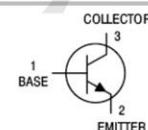
APPLICATIONS

- Switching application.

Package and Pin Configuration



SOT-23



Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	1	A
P_C	Collector Dissipation	500	mW
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	°C

Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(\text{BR})\text{CBO}}$	$I_C=100\mu\text{A}, I_E=0$	80			V
Collector-emitter breakdown voltage	$V_{(\text{BR})\text{CEO}}$	$I_C=10\text{mA}, I_B=0$	60			V
Emitter-base breakdown voltage	$V_{(\text{BR})\text{EBO}}$	$I_E=100\mu\text{A}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{\text{CB}}=60\text{V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{\text{EB}}=4\text{V}, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{\text{CE}}=5\text{V}, I_C=1\text{mA}$	100			
		$V_{\text{CE}}=5\text{V}, I_C=500\text{mA}$	100		300	
		$V_{\text{CE}}=5\text{V}, I_C=1\text{A}$	80			
		$V_{\text{CE}}=5\text{V}, I_C=2\text{A}$	30			
Collector-emitter saturation voltage	$V_{\text{CE}(\text{sat})}$	$I_C=500\text{mA}, I_B=50\text{mA}$ $I_C=1\text{A}, I_B=100\text{mA}$			0.25 0.5	V
Base-emitter saturation voltage	$V_{\text{BE}(\text{sat})}$	$I_C=1\text{A}, I_B=100\text{mA}$			1.1	V
Base-emitter voltage	$V_{\text{BE}(\text{on})}$	$I_C=1\text{A}, V_{\text{CE}}=5\text{V}$			1.0	V
Transition frequency	f_T	$V_{\text{CE}}=10\text{V}, I_C=50\text{mA}$ $f=100\text{MHz}$	150			MHz
Collector output capacitance	C_{ob}	$V_{\text{CB}}=10\text{V}, f=1\text{MHz}$			10	pF



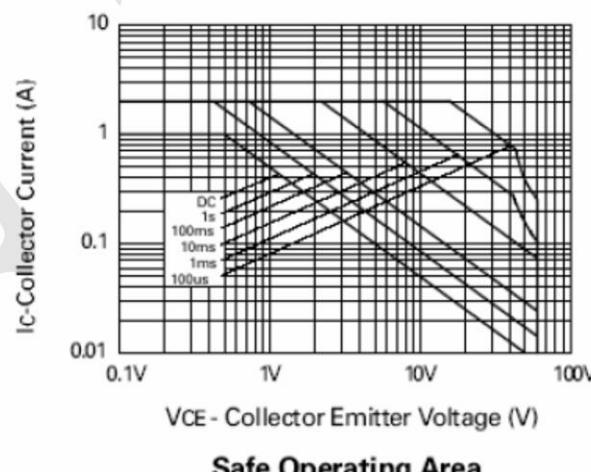
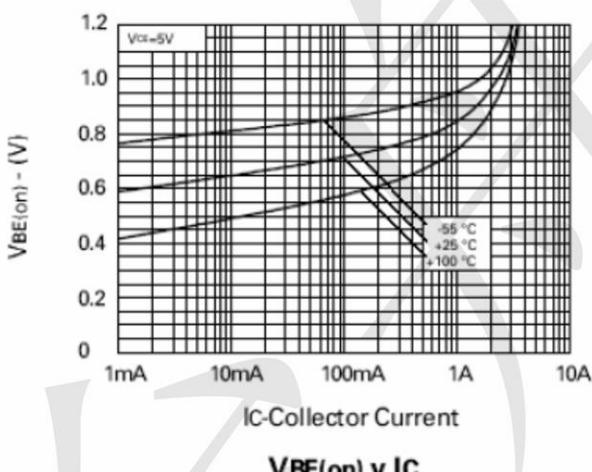
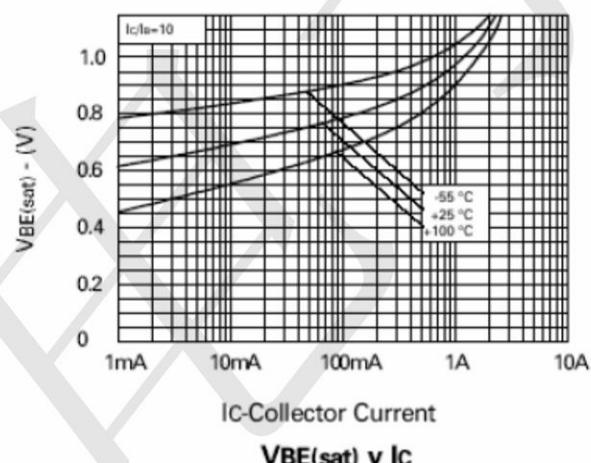
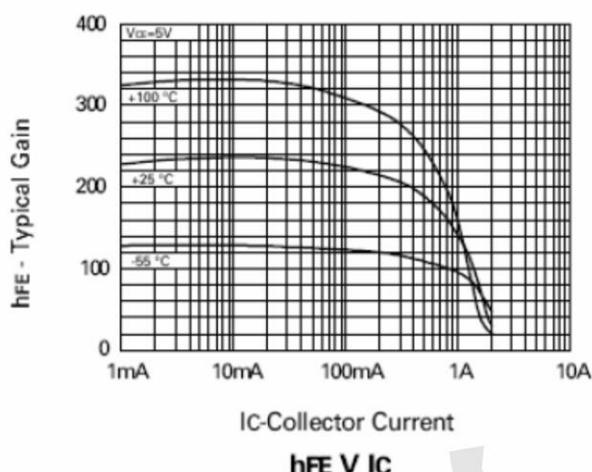
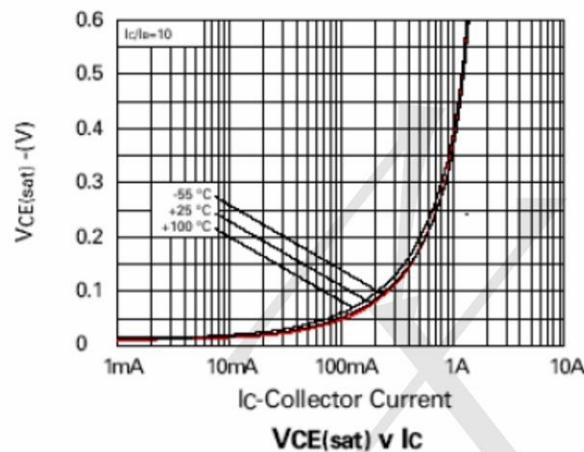
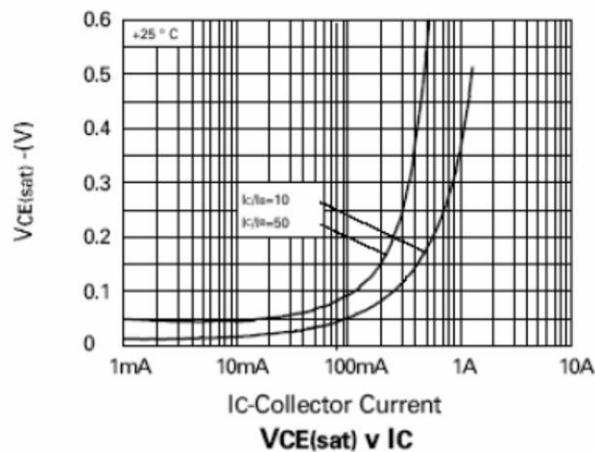
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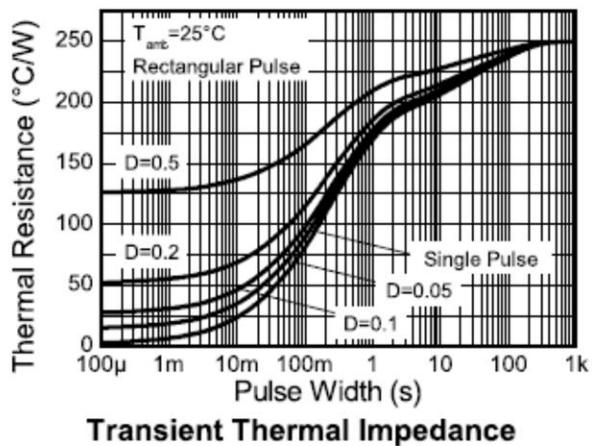
FMMT491

NPN Silicon Epitaxial Planar Transistor

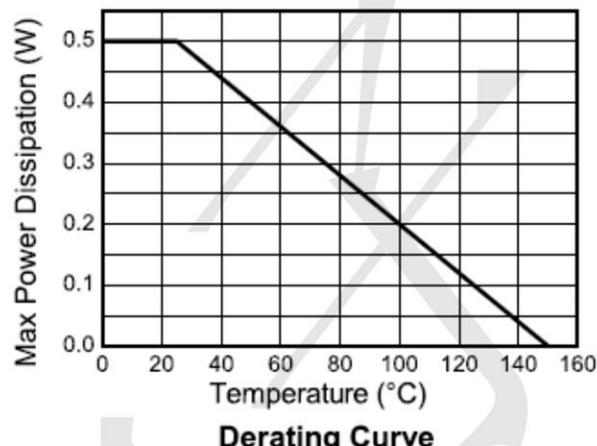
Typical Electrical and Thermal Characteristics

www.sot23.com.tw



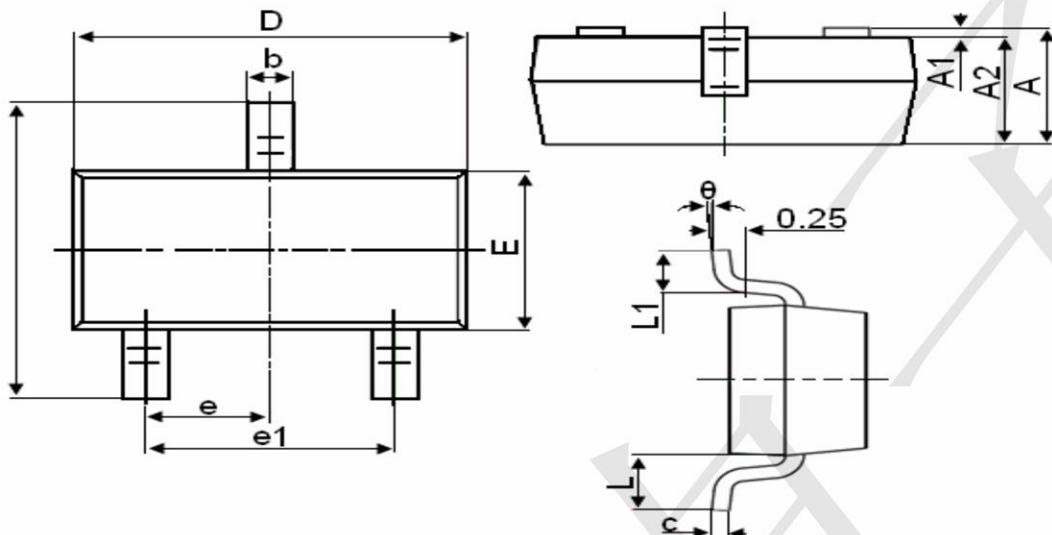


Transient Thermal Impedance



Derating Curve

Package Outline Dimensions (SOT-23)



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°